

MOSFET

OptiMOS™5 Power-Transistor, 100 V

Features

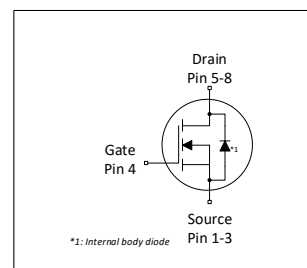
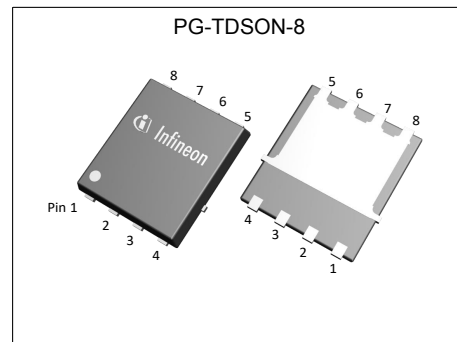
- Ideal for high-frequency switching
- Optimized for charger
- 100% avalanche tested
- Superior thermal resistance
- N-channel, logic level
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product validation

Qualified according to JEDEC Standard

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(on),max}$	5.4	mΩ
I_D	97	A
Q_{oss}	50	nC
$Q_G(0V..4.5V)$	20	nC



RoHS

Type / Ordering Code	Package	Marking	Related Links
ISC0806NLS	PG-TDSON-8	0806NL	-

Table of Contents

Description 1

Maximum ratings 3

Thermal characteristics 3

Electrical characteristics 4

Electrical characteristics diagrams 6

Package Outlines 10

Revision History 11

Trademarks 11

Disclaimer 11

1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	97 74 16	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$, $T_A=25\text{ °C}$, $R_{thJA}=50\text{ °C/W}^{2)}$
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	388	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse ⁴⁾	E_{AS}	-	-	93	mJ	$I_D=50\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	96 2.5	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$, $R_{thJA}=50\text{ °C/W}^{2)}$
Operating and storage temperature	T_j, T_{stg}	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	0.7	1.3	°C/W	-
Thermal resistance, junction - case, top	R_{thJC}	-	-	20	°C/W	-
Device on PCB, 6 cm ² cooling area ²⁾	R_{thJA}	-	-	50	°C/W	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See Diagram 3 for more detailed information

⁴⁾ See Diagram 13 for more detailed information

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	1.1	1.6	2.3	V	$V_{DS}=V_{GS}$, $I_D=61\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	5.0 6.5	5.4 7.1	m Ω	$V_{GS}=10\text{ V}$, $I_D=50\text{ A}$ $V_{GS}=4.5\text{ V}$, $I_D=25\text{ A}$
Gate resistance ¹⁾	R_G	-	1.2	-	Ω	-
Transconductance	g_{fs}	-	89	-	S	$ V_{DS} \geq 2 I_D /R_{DS(on)max}$, $I_D=50\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance ¹⁾	C_{iss}	-	2600	3400	pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Output capacitance ¹⁾	C_{oss}	-	420	560	pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance ¹⁾	C_{rss}	-	19	25	pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	3.7	-	ns	$V_{DD}=50\text{ V}$, $V_{GS}=4.5\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r	-	5.4	-	ns	$V_{DD}=50\text{ V}$, $V_{GS}=4.5\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	14	-	ns	$V_{DD}=50\text{ V}$, $V_{GS}=4.5\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Fall time	t_f	-	7.0	-	ns	$V_{DD}=50\text{ V}$, $V_{GS}=4.5\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$

Table 6 Gate charge characteristics²⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	8.4	-	nC	$V_{DD}=50\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	4.5	-	nC	$V_{DD}=50\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate to drain charge	Q_{gd}	-	6.9	-	nC	$V_{DD}=50\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Switching charge	Q_{sw}	-	11	-	nC	$V_{DD}=50\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge total ¹⁾	Q_g	-	20	26	nC	$V_{DD}=50\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	3.2	-	V	$V_{DD}=50\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge total ¹⁾	Q_g	-	37	49	nC	$V_{DD}=50\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge	Q_{oss}	-	50	-	nC	$V_{DS}=50\text{ V}$, $V_{GS}=0\text{ V}$

¹⁾ Defined by design. Not subject to production test.

²⁾ See "Gate charge waveforms" for parameter definition

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	81	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	388	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.89	1.1	V	$V_{GS}=0\text{ V}$, $I_F=50\text{ A}$, $T_j=25\text{ °C}$
Reverse recovery time ¹⁾	t_{rr}	-	49	-	ns	$V_R=50\text{ V}$, $I_F=50\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge ¹⁾	Q_{rr}	-	67	-	nC	$V_R=50\text{ V}$, $I_F=50\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$

¹⁾ Defined by design. Not subject to production test.

4 Electrical characteristics diagrams

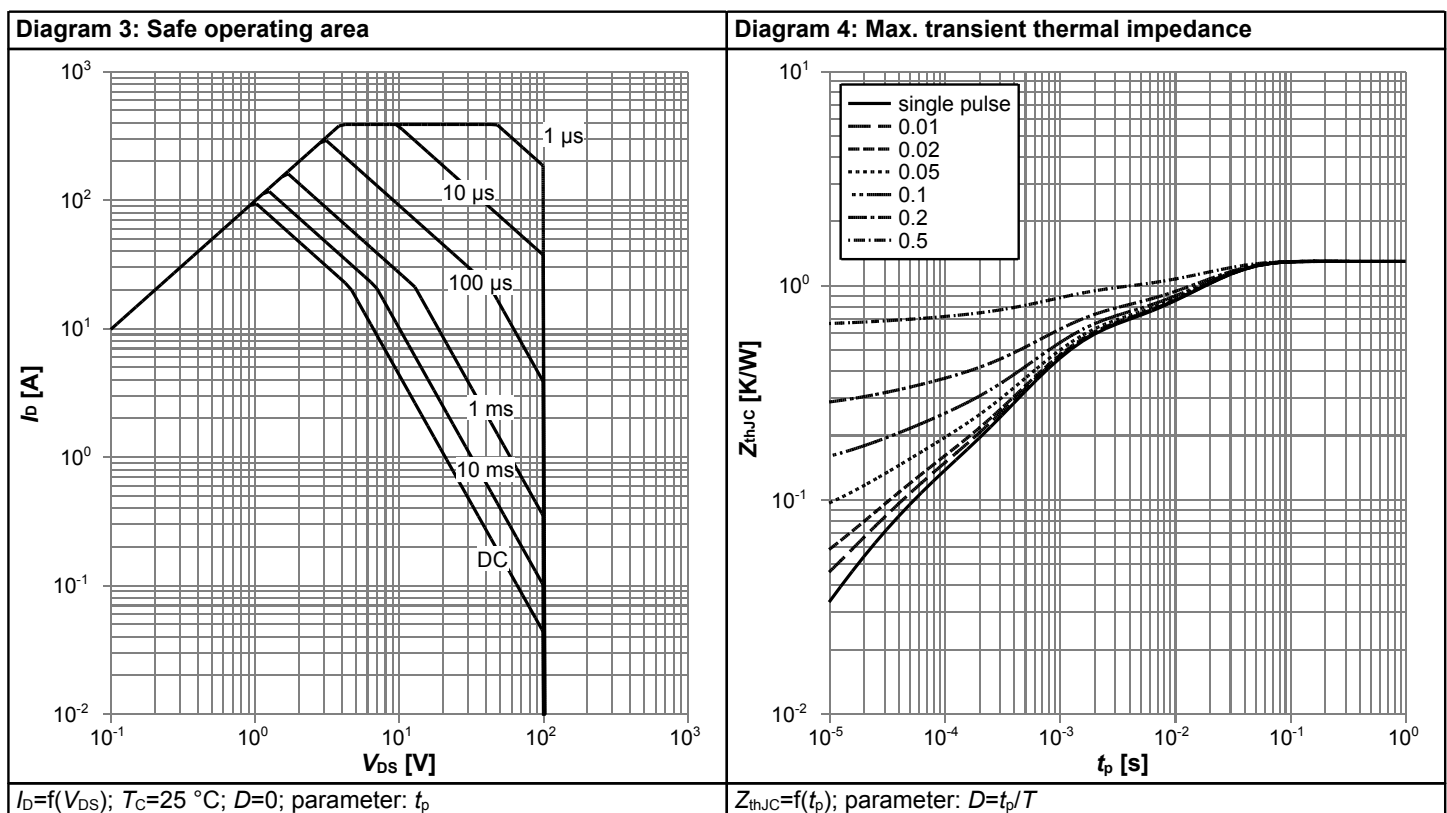
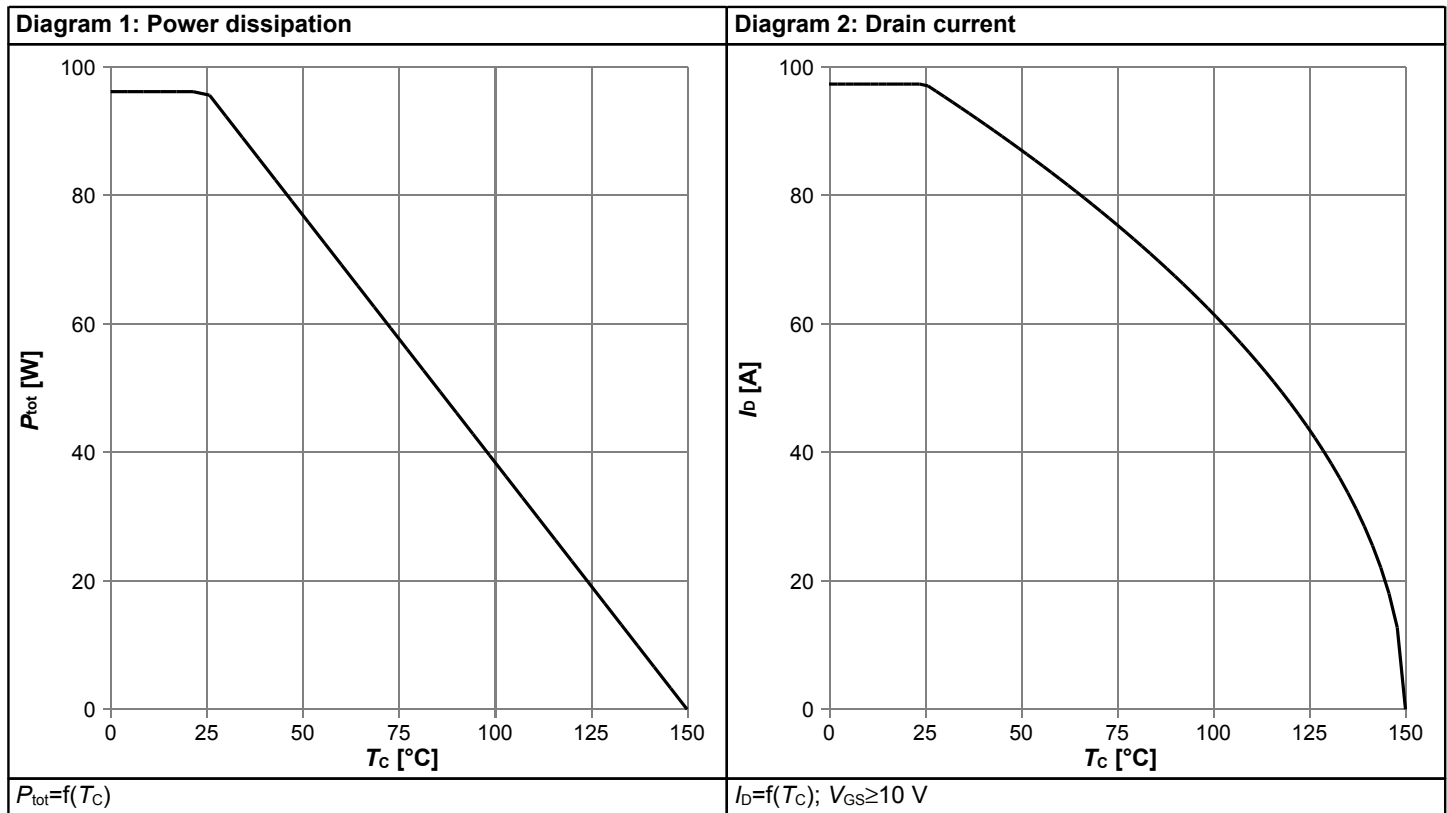
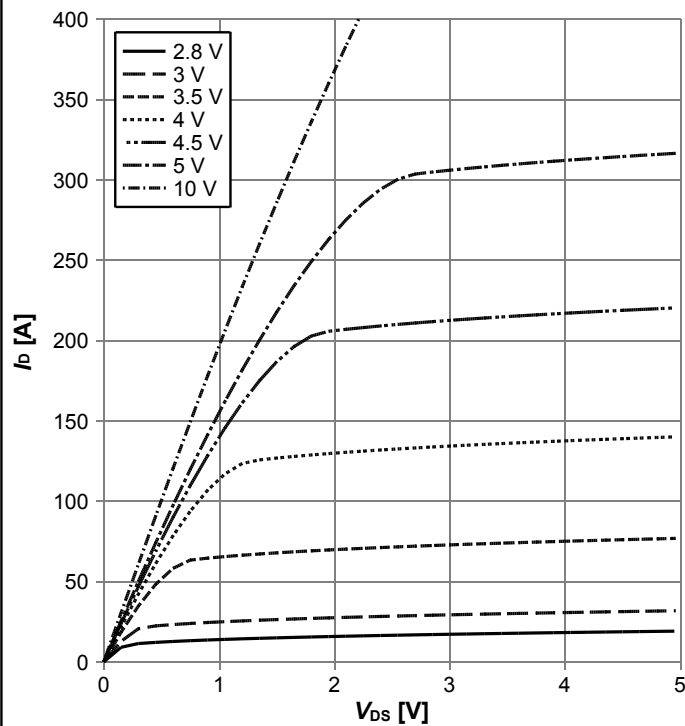
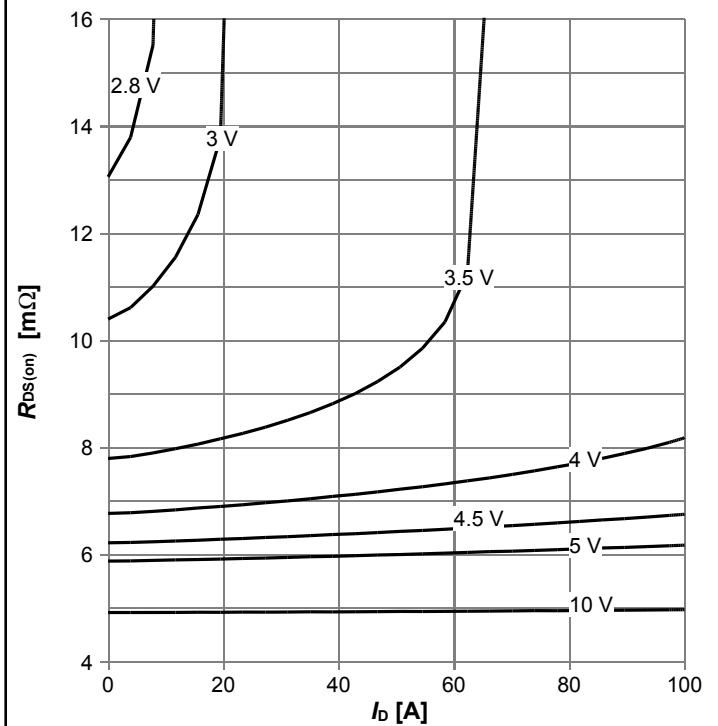


Diagram 5: Typ. output characteristics



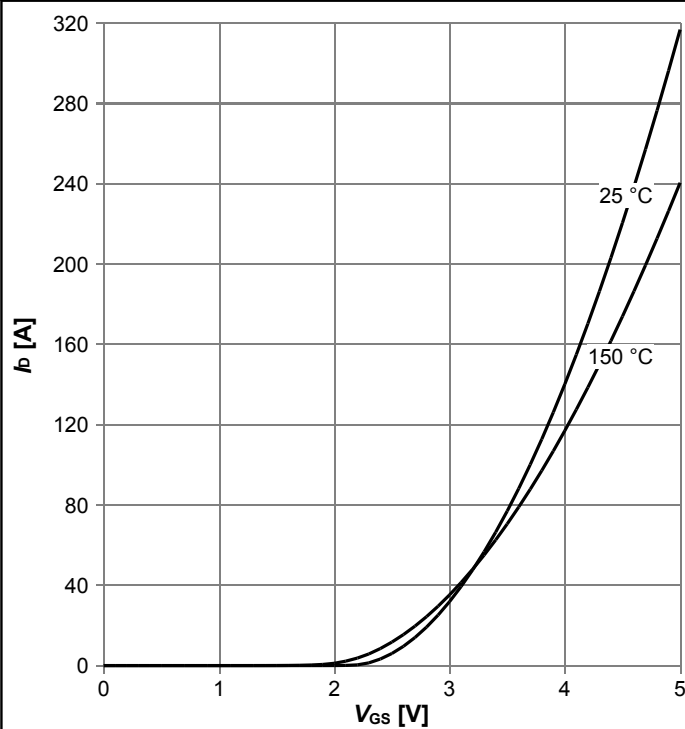
$I_D = f(V_{DS})$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



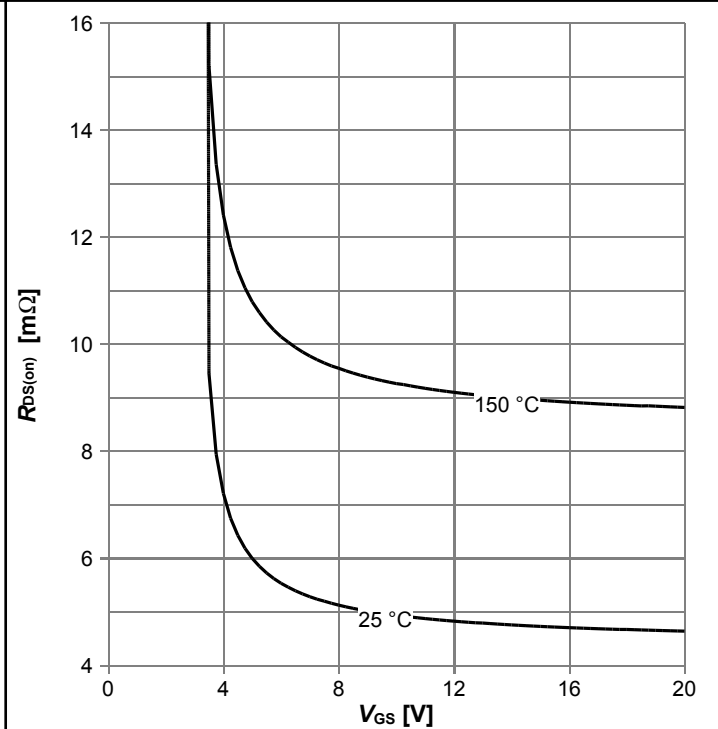
$R_{DS(on)} = f(I_D)$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



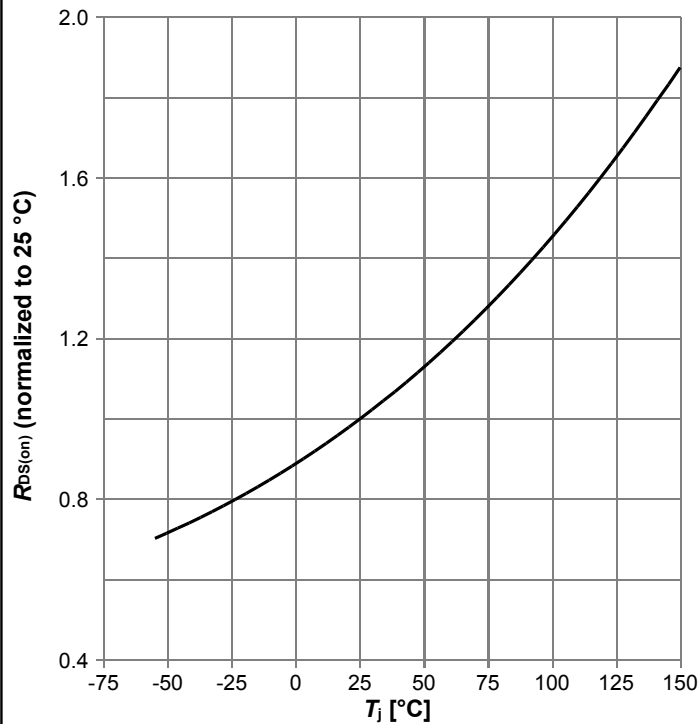
$I_D = f(V_{GS})$, $|V_{DS}| > 2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



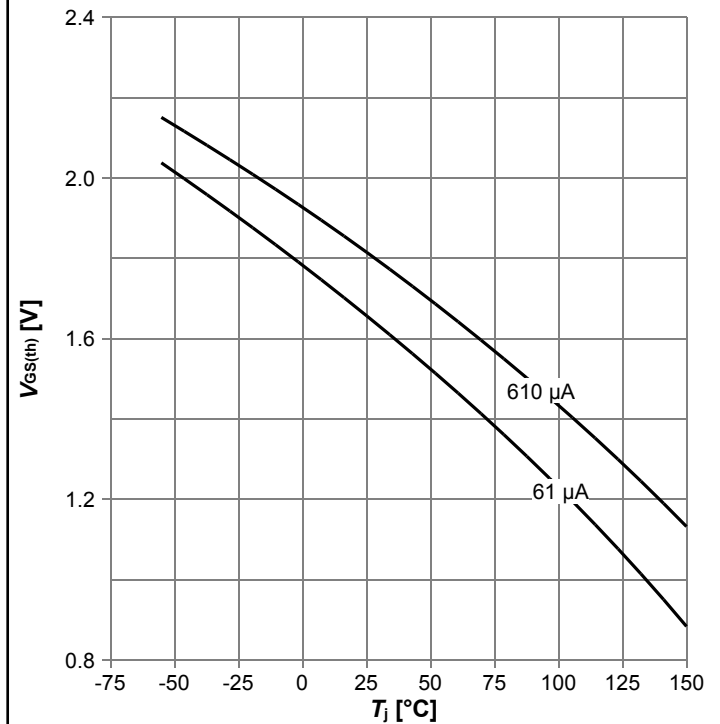
$R_{DS(on)} = f(V_{GS})$, $I_D = 50\text{ A}$; parameter: T_j

Diagram 9: Normalized drain-source on resistance



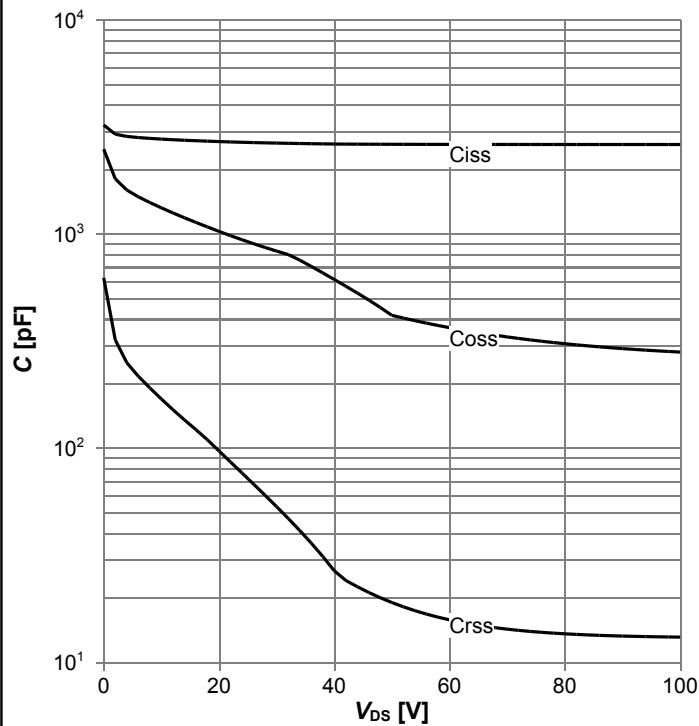
$$R_{DS(on)} = f(T_j), I_D = 50 \text{ A}, V_{GS} = 10 \text{ V}$$

Diagram 10: Typ. gate threshold voltage



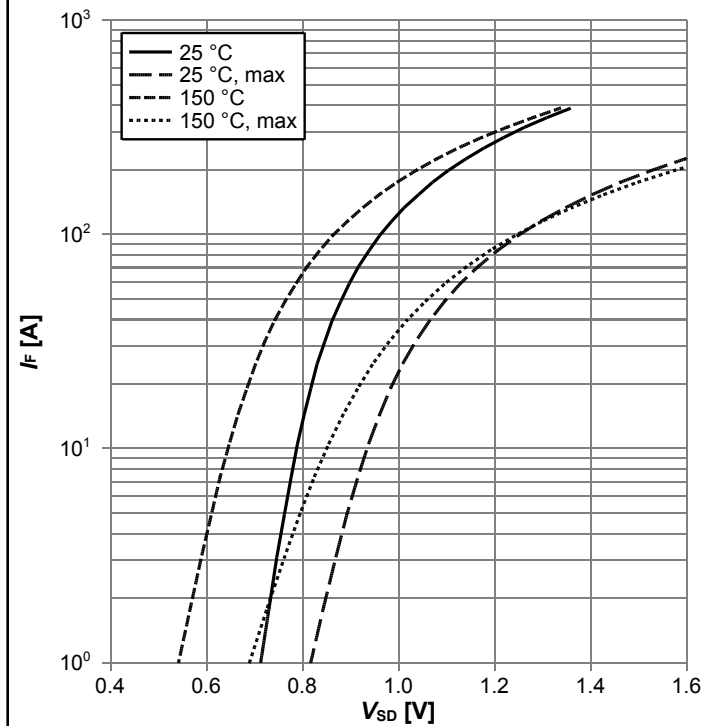
$$V_{GS(th)} = f(T_j), V_{GS} = V_{DS}; \text{ parameter: } I_D$$

Diagram 11: Typ. capacitances



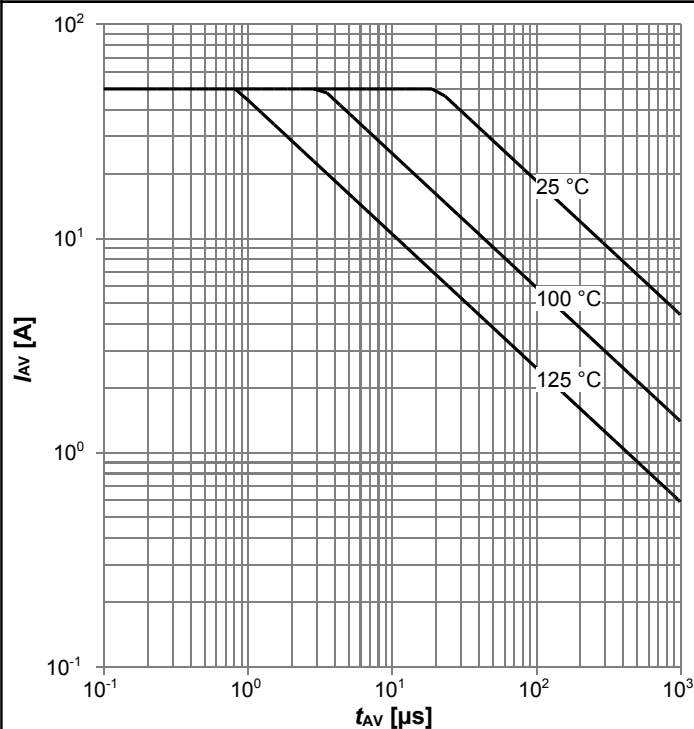
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

Diagram 12: Forward characteristics of reverse diode



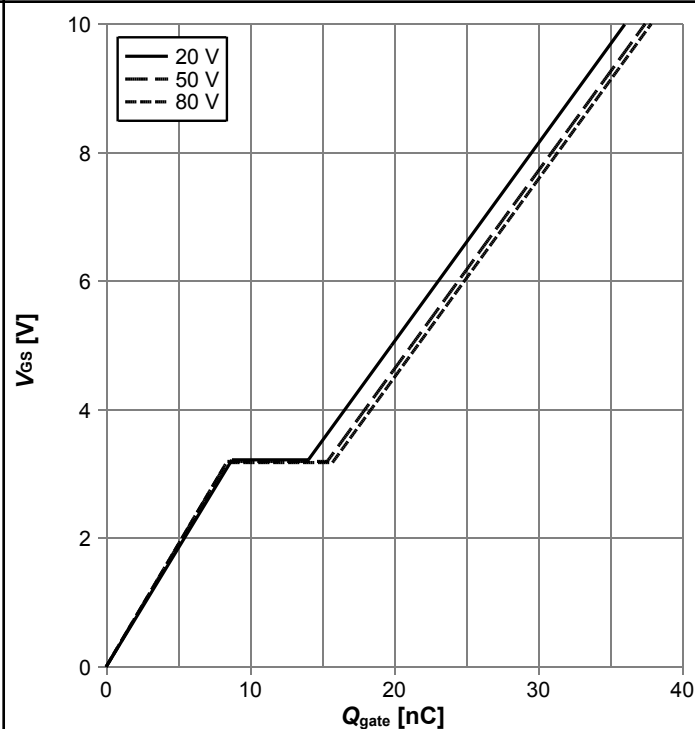
$$I_F = f(V_{SD}); \text{ parameter: } T_j$$

Diagram 13: Avalanche characteristics



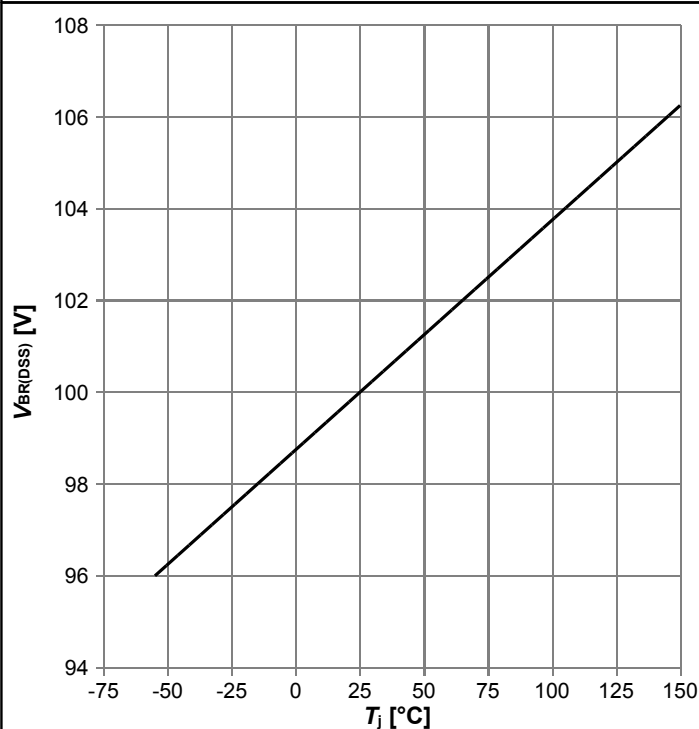
$I_{AS}=f(t_{AV})$; $R_{GS}=25 \Omega$; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



$V_{GS}=f(Q_{gate})$, $I_D=50$ A pulsed, $T_j=25$ °C; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

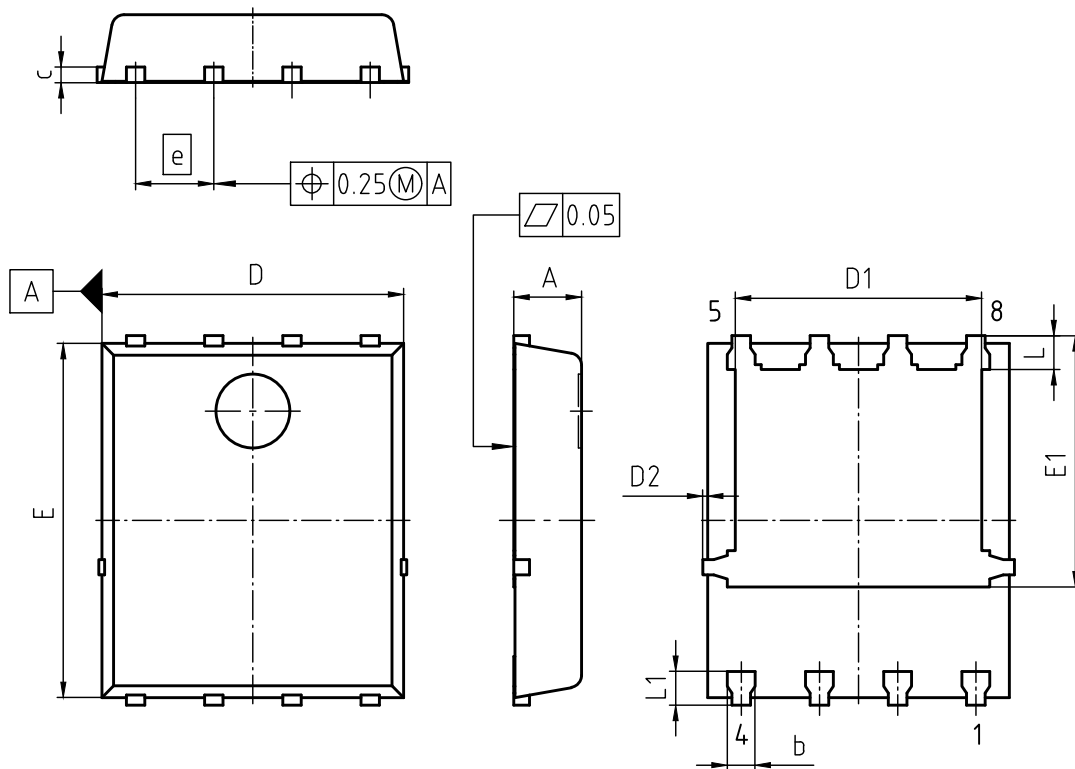


$V_{BR(DSS)}=f(T_j)$; $I_D=1$ mA

Diagram Gate charge waveforms



5 Package Outlines



PACKAGE - GROUP NUMBER: PG-TDSON-8-U08		
REVISION: 01	DATE: 12.02.2021	
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	0.90	1.20
b	0.34	0.54
c	0.15	0.35
D	4.80	5.35
D1	3.90	4.40
D2	0.00	0.22
E	5.70	6.10
E1	4.05	4.25
e	1.27	
L	0.45	0.65
L1	0.45	0.65

- 1) EXCLUDING MOLD FLASH
- 2) REMOVAL ON MOLD GATE
INTRUSION 0.1 MM
PROTRUSION 0.1 MM
- 3) ALL METAL SURFACES ARE PLATED,
EXCEPT AREA OF CUT

Figure 1 Outline PG-TDSON-8, dimensions in mm

Revision History

ISC0806NLS

Revision: 2021-04-01, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2021-03-15	Release of final version
2.1	2021-04-01	Update of features list

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